CPH3348

Power MOSFET
–12V, 70mΩ, –3A, Single P-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

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Features

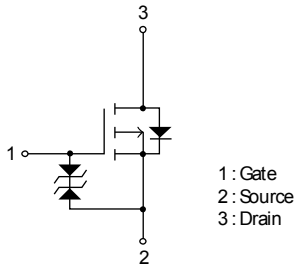
- Low On-Resistance
- 1.8V drive
- Pb-Free and RoHS compliance
- Halogen Free compliance : CPH3348-TL-W

Typical Applications

- Load Switch
- DC/DC Converter

V_{DSS}	R_{DS}(on) Max	I_D Max
–12V	70mΩ@ –4.5V	–3A
	115mΩ@ –2.5V	
	215mΩ@ –1.8V	

ELECTRICAL CONNECTION
P-Channel



SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1, 2)

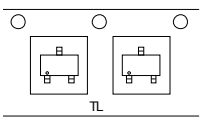
Parameter	Symbol	Value	Unit
Drain to Source Voltage	V_{DSS}	–12	V
Gate to Source Voltage	V_{GSS}	±10	V
Drain Current (DC)	I_D	–3	A
Drain Current (Pulse) PW ≤ 10μs, duty cycle ≤ 1%	I_{DP}	–12	A
Power Dissipation When mounted on ceramic substrate (1200mm^2 × 0.8mm)	P_D	1.0	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

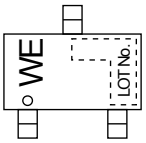
2 : This product is designed to "ESD immunity<200V*", so please take care when handling.

*Machine Model

PACKING TYPE : TL



MARKING



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (1200mm^2 × 0.8mm)	$R_{\theta JA}$	125	°C/W

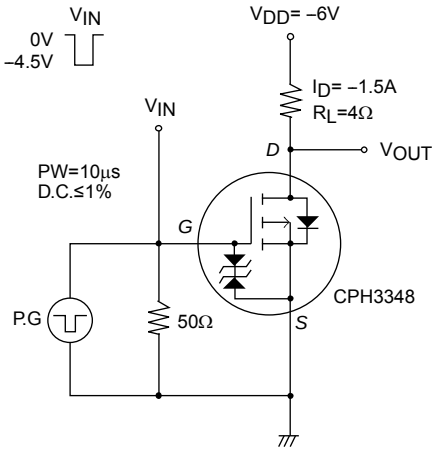
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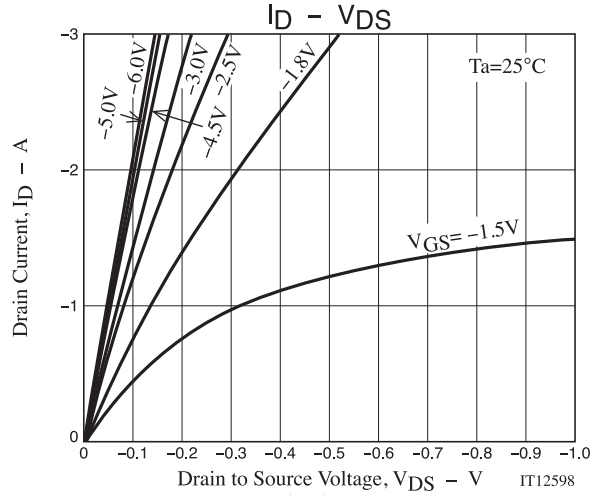
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 3)

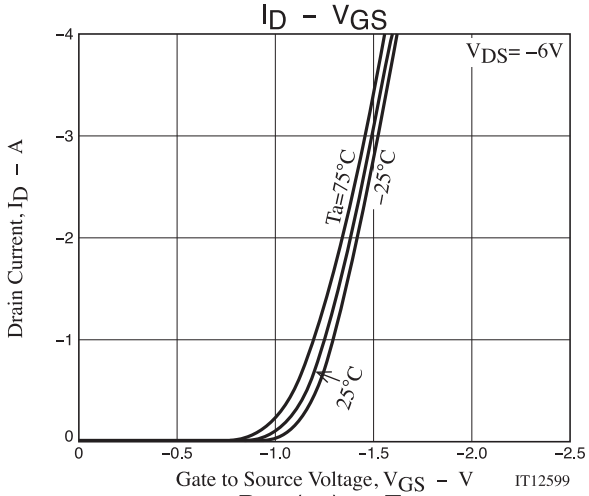
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0V	−12			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−12V, V_{GS}=0V			−10	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Gate Threshold Voltage	$V_{GS}(th)$	V_{DS}=−6V, I_D=−1mA	−0.4		−1.4	V
Forward Transconductance	g_{FS}	V_{DS}=−6V, I_D=−1.5A		4.3		S
Static Drain to Source On-State Resistance	$R_{DS}(on)1$	I_D=−1.5A, V_{GS}=−4.5V		54	70	mΩ
	$R_{DS}(on)2$	I_D=−0.8A, V_{GS}=−2.5V		80	115	mΩ
	$R_{DS}(on)3$	I_D=−0.3A, V_{GS}=−1.8V		125	215	mΩ
Input Capacitance	Ciss	V_{DS}=−6V, f=1MHz		405		pF
Output Capacitance	Coss			145		pF
Reverse Transfer Capacitance	Crss			100		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit		8.8		ns
Rise Time	t_r			80		ns
Turn-OFF Delay Time	$t_d(off)$			41		ns
Fall Time	t_f			50		ns
Total Gate Charge	Qg	V_{DS}=−6V, V_{GS}=−4.5V, I_D=−3A		5.6		nC
Gate to Source Charge	Qgs			0.7		nC
Gate to Drain “Miller” Charge	Qgd			1.6		nC
Forward Diode Voltage	V_{SD}	I_S=−3A, V_{GS}=0V		−0.85	−1.2	V

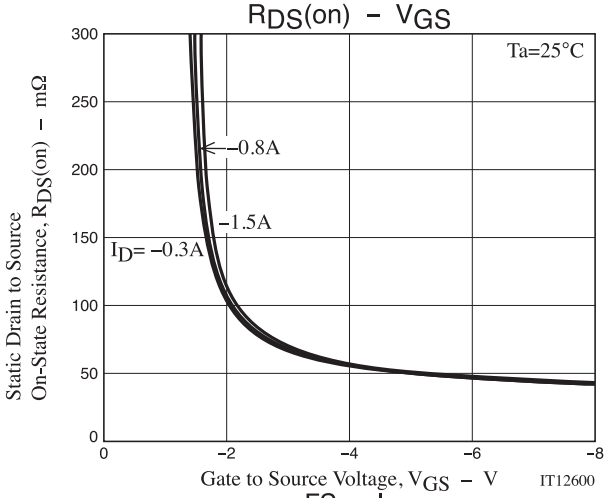
Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

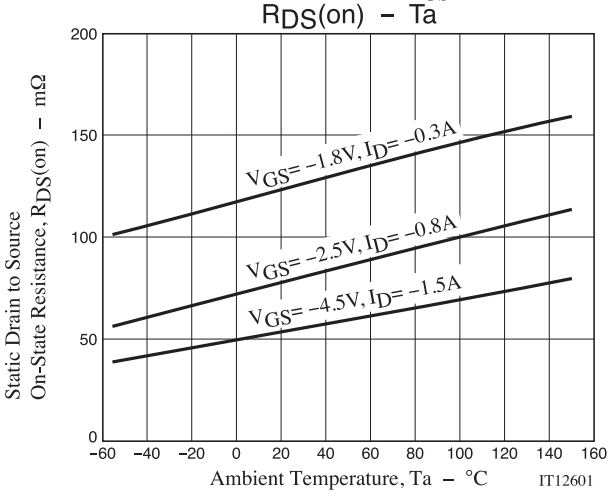
Switching Time Test Circuit

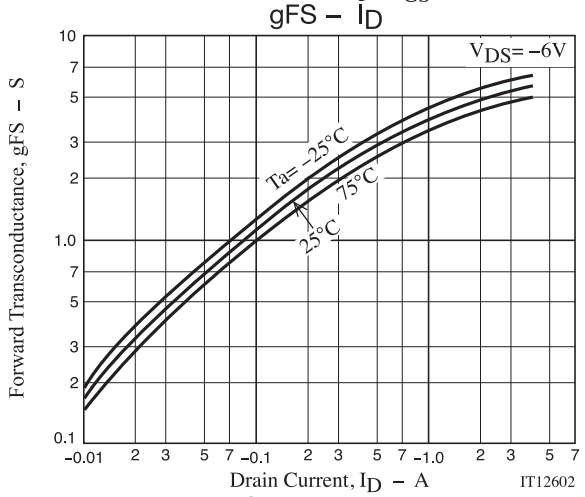


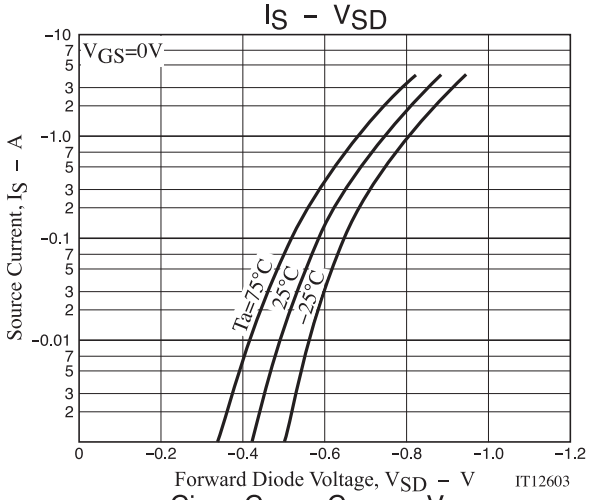

ID – VDS
Ta=25°C
–5.0V
–6.0V
–3.0V
–4.5V
–2.5V
–1.8V
VGS= –1.5V
Drain Current, ID – A
Drain to Source Voltage, VDS – V
IT12598

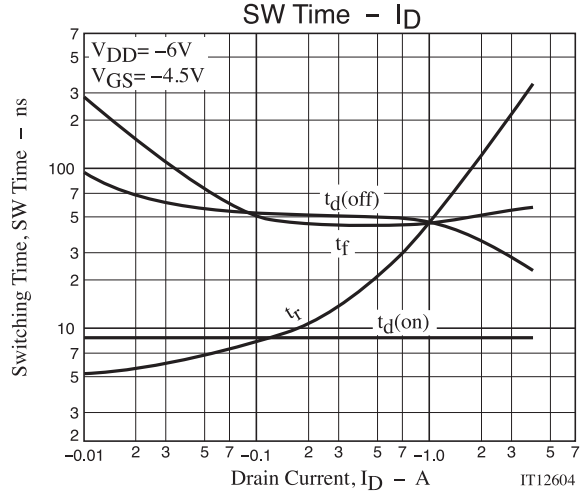

ID – VGS
VDS= –6V
Ta=75°C
–25°C
25°C
Drain Current, ID – A
Gate to Source Voltage, VGS – V
IT12599

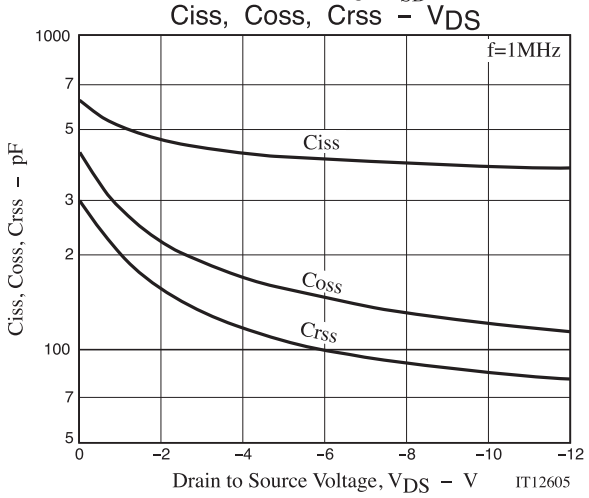

RDS(on) – VGS
Ta=25°C
–0.8A
–1.5A
ID= –0.3A
Static Drain to Source On-State Resistance, RDS(on) – mΩ
Gate to Source Voltage, VGS – V
IT12600

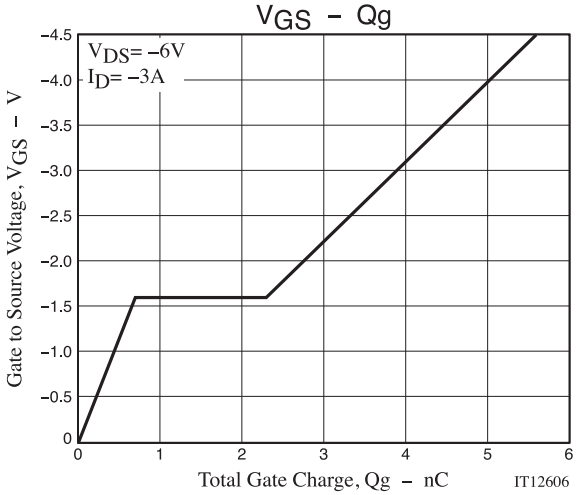

RDS(on) – Ta
VGS= –1.8V, ID= –0.3A
VGS= –2.5V, ID= –0.8A
VGS= –4.5V, ID= –1.5A
Static Drain to Source On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT12601

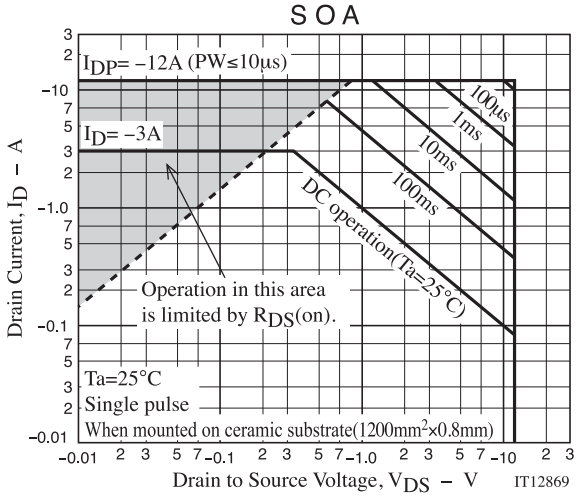

gFS – ID
VDS= –6V
Ta= –25°C
75°C
25°C
Forward Transconductance, gFS – S
Drain Current, ID – A
IT12602

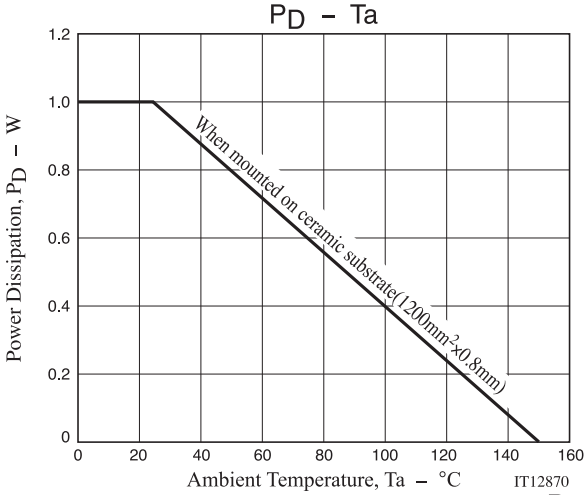

IS – VSD
VGS=0V
Ta=75°C
25°C
–25°C
Source Current, IS – A
Forward Diode Voltage, VSD – V
IT12603

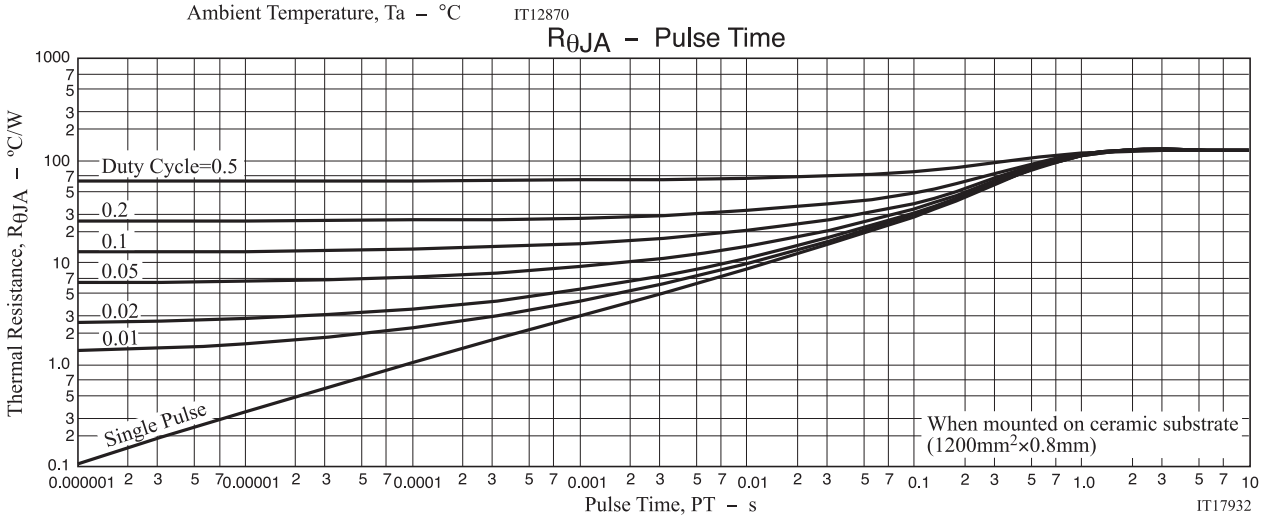

SW Time – ID
VDD= –6V
VGS= –4.5V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT12604


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain to Source Voltage, VDS – V
IT12605


VGS – Qg
VDS= –6V
ID= –3A
Gate to Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT12606


S O A
IDP= –12A (PW≤10μs)
ID= –3A
100μs
1ms
10ms
100ms
DC operation(Ta=25°C)
Operation in this area
is limited by RDS(on).
Ta=25°C
Single pulse
When mounted on ceramic substrate(1200mm2×0.8mm)
Drain Current, ID – A
Drain to Source Voltage, VDS – V
IT12869

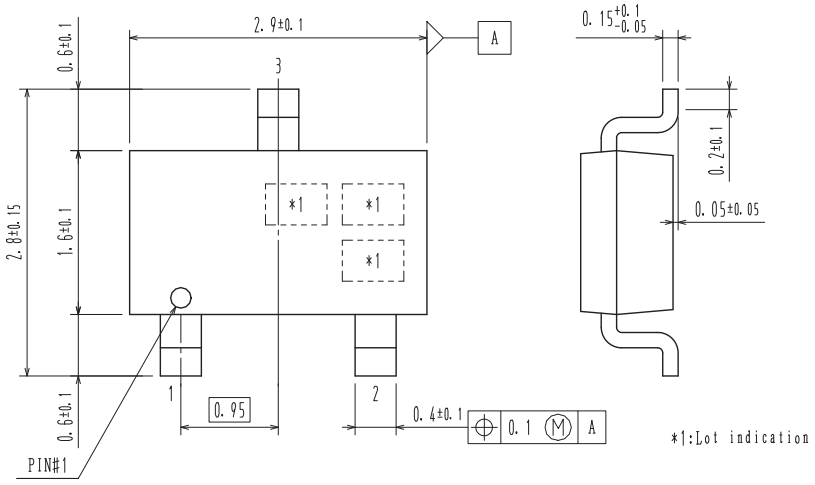

PD – Ta
When mounted on ceramic substrate(1200mm2×0.8mm)
Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT12870

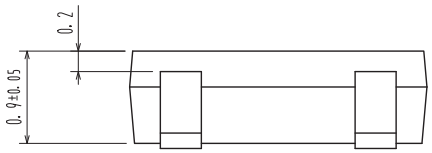

RθJA – Pulse Time
Duty Cycle=0.5
0.2
0.1
0.05
0.02
0.01
Single Pulse
When mounted on ceramic substrate
(1200mm2×0.8mm)
Thermal Resistance, RθJA – °C/W
Pulse Time, PT – s
IT17932

PACKAGE DIMENSIONS

unit : mm

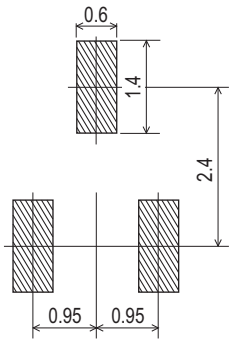
CPH3
CASE 318BA
ISSUE O





1 : Gate
2 : Source
3 : Drain

Recommended Soldering Footprint



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
CPH3348-TL-E	WE	CPH3 SC-59, SOT-23, TO-236 (Pb-Free)	3,000 / Tape & Reel
CPH3348-TL-W		CPH3 SC-59, SOT-23, TO-236 (Pb-Free / Halogen Free)	

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the CPH3348 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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